

Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

M/A-COM Products Released - Rev. 07.07

Designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode–S transmitters.

- Guaranteed performance @ 1090 MHz
 Output power = 150 W Peak
 Gain = 9.5 dB min, 10.0 dB (typ.)
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Hermetically sealed package
- Silicon nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input and output matching
- Characterized with 10 μs, 10% duty cycle pulses
- Recommended driver for a pair of MRF10500 transistors

Product Image

CASE 376B-02, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CES}	65	Vdc
Collector-Base Voltage	V _{CBO}	65	Vdc
Emitter-Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Peak (1)	Ic	14	Adc
Total Device Dissipation @ T _C = 25°C (1), (2) Derate above 25°C	P _D	700 4.0	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +200	°C
Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	R _{eJC}	0.25	°C/W

NOTES:

- Under pulse RF operating conditions.
- These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
- Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 10 μs, 10%.)

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.



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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

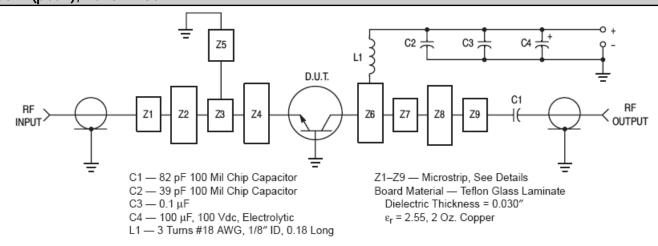
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•			
Collector–Emitter Breakdown Voltage (I _C = 60 mAdc, V _{BE} = 0)	V _{(BR)CES}	65	_	_	Vdc
Collector-Base Breakdown Voltage (I _C = 60 mAdc, I _E = 0)	V _{(BR)CBO}	65	_	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0)	V _{(BR)EBO}	3.5	_	_	Vdc
Collector Cutoff Current (V _{CB} = 36 Vdc, I _E = 0)	I _{CBO}	_	_	25	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 5.0 Vdc)	h _{FE}	20	_	_	_
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 150 W Peak, f = 1090 MHz)	G _{PB}	9.5	10	_	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 150 W Peak, f = 1090 MHz)	η	40	_	_	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 150 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power			

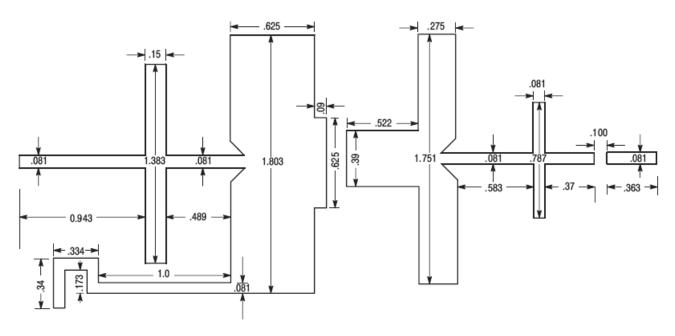
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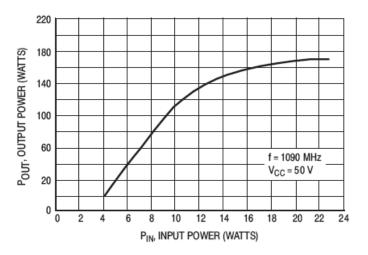


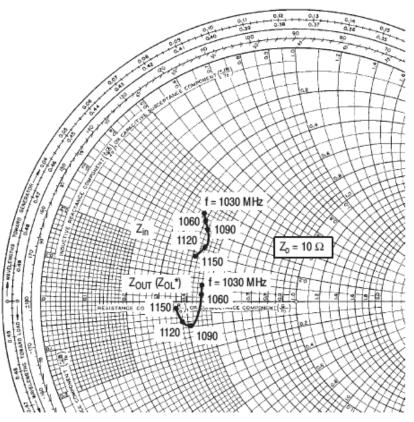
Figure 2. Output Power versus Input Power

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P_{OUT} = 150 W Pk V_{CC} = 50 V

Z _{OUT})
MS
j0.7
j0.3
j1.0
j0.8
j0.3
֡

 Z_{OL}^{\star} is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

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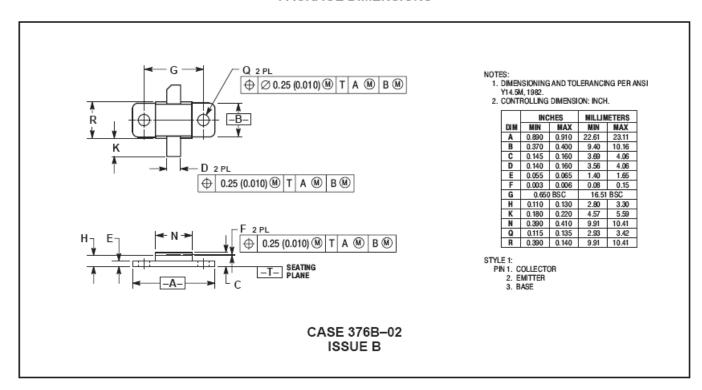
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PACKAGE DIMENSIONS



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